



2018년 2월 7일(수), 13:15-14:45

Room D (함백II+III, 5층)

E. Compound Semiconductors 분과

[WD3-E] GaN Device

WD3-E-1 13:15-13:30	Enhancement of Gate Controllability and Suppression of Current Collapse in AlGaIn/GaN HEMT Fabricated on GaN-Based Cantilever Quan Dai, Dong-Hyeok Son, Ryun-Hwi Kim, Jun-Hyeok Lee, Terirama Thingujam, Jung-Min Ju, and Jung-Hee Lee <i>School of electronics engineering, Kyungpook National University</i>
WD3-E-2 13:30-13:45	Improvement of Bias-Induced Vth Stability in Recessed-Gate AlGaIn/GaN MIS-HEMTs with Nitrogen-Incorporated Al₂O₃ Gate Insulator Myoung-Jin Kang ¹ , Cheol-Hee Lee ¹ , Su-Keun Eom ¹ , Jae-Gil Lee ¹ , Ho-Young Cha ² , and Kwang-Seok Seo ¹ <i>¹Department of Electrical and Computer Engineering and Inter-University Semiconductor Research Center, Seoul National University, ²Department of Electronic and Electrical Engineering, Hongik University</i>
WD3-E-3 13:45-14:00	Proton Irradiation Effects on AlGaIn/GaN HEMT Isolated by Ion Implantation Dong-Seok Kim ¹ , Sun Mog Yeo ¹ , Jun-Hyeok Lee ² , and Jung-Hee Lee ² <i>¹Korea Multi-Purpose Accelerator Complex, KAERI, ²School of Electronics Engineering, Kyungpook National University</i>
WD3-E-4 14:00-14:15	Low Energy Proton Irradiation Effects in AlGaIn/GaN-on-Si HEMTs Dongmin Keum, Geunho Cho, and Hyungtak Kim <i>Department of Electronic and Electrical Engineering, Hongik University</i>
WD3-E-5 14:15-14:30	The Characteristic of GaN Vertical Nanowire for Low Voltage Application Dong-Hyeok Son, Quan Dai, Ryun-Hwi Kim, Jun-Hyeok Lee, Hyun-Su Lee, and Jung-Hee Lee <i>School of Electronics Engineering, Kyungpook National University</i>
WD3-E-6 14:30-14:45	Development of 4-Inch AlGaIn/GaN High Electron Mobility Transistors Grown on Semi-Insulating SiC Substrate with High Electron Mobility Chu-Young Cho, Yumin Koh, Hyeong-Ho Park, and Kyung-Ho Park <i>Electronic Devices Laboratory, KANC</i>